

Line-up and Main Specifications of New SiC Schottky Barrier Diodes:

	Characteristics (Ta=25°C)	Absolute Maximum Ratings			Electrical Characteristics			
		Forward DC Current	Non-repetitive Peak Forward Surge Current	Power Dissipation	Forward Voltage	Anode-cathode On-resistance	Junction Capacitance	Total Capacitive Charge
	Symbol	$I_{F(DC)}$	I_{FSM}	P_{tot}	V_F	R_{ON}	C_j	Q_C
Package	Value	Max	Max	Max	Typ. & Max	Typ.	Typ.	Typ.
	Unit	(A)	(A)	(W)	(V)	(mΩ)	(pF)	(nC)
	Test Conditions / Part Number	—	@ Half-sine Wave t = 10 ms	—	@ $I_{F(DC)}$	@ $I_{F(DC)} \times 0.25$ to 1.0	@ $V_R = 1V$	@ $V_R = 400V$
Non-Isolation TO-220 -2L	TRS4E65F	4	39	55.6	1.45	120	165	10.4
	TRS6E65F	6	55	68.2	(Typ.)	82	230	15.1
	TRS8E65F	8	69	83.3	1.6 (Max)	62	300	19.7
	TRS10E65F	10	83	107		48	400	24.4
Isolation TO-220F -2L	TRS4A65F	4	37	33.6	1.45	120	165	10.4
	TRS6A65F	6	52	35.4	(Typ.)	82	230	15.1
	TRS8A65F	8	65	37.5	1.6 (Max)	62	300	19.7
	TRS10A65F	10	79	39.7		48	400	24.4

Notes

[1] R_{ON} : Anode-cathode on-resistance, Q_C : Total capacitive charge